

Notice of References Cited	Application/Control No. 10/639,465	Applicant(s)/Patent Under Reexamination YAMAZAKI ET AL.	
	Examiner George A. Goudreau	Art Unit 1792	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,132,806	10-2000	Dutartre, Didier	427/255.18
	B	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	"High-resolution reactive ion etching and damage effects in the silicon/ germanium silicon system"; Journal of Vacuum Science & Technology: B; (1993'); 11 (6); pp. 2224-2228; Cheung et. al.
	V	"Reactive ion etching of Si/SiGe in CF4/Ar and Cl2/BCl3/Ar discharges"; Materials Chemistry and Physics; (1999'); 60 (1); Chang et. al.; pp. 22-27
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	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.